

8367 D-channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-20V	60mΩ@-4.5V	-2.8A
	85mΩ@-2.0V	
	160mΩ@-1.5V	

SOT-23



1. GATE
2. SOURCE
3. DRAIN

FEATURE

- TrenchFET Power MOSFET
- Excellent $R_{DS(on)}$ and Low Gate Charge

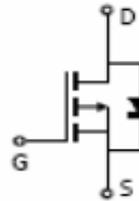
APPLICATION

- DC/DC Converter
- Load Switch for Portable Devices
Battery Switch

MARKING



Equivalent Circuit



ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

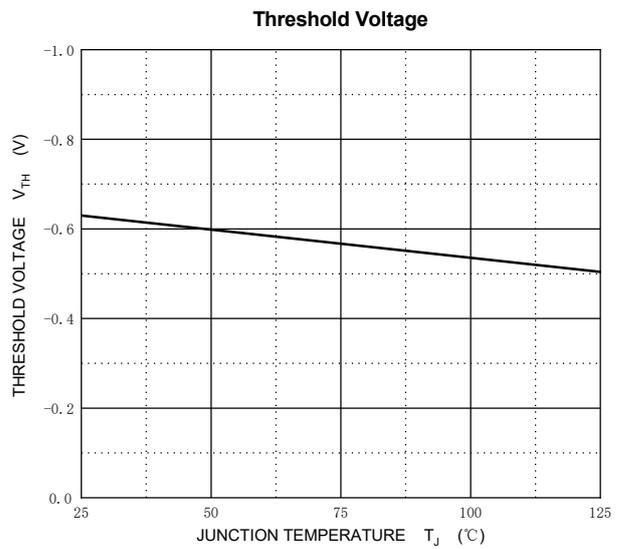
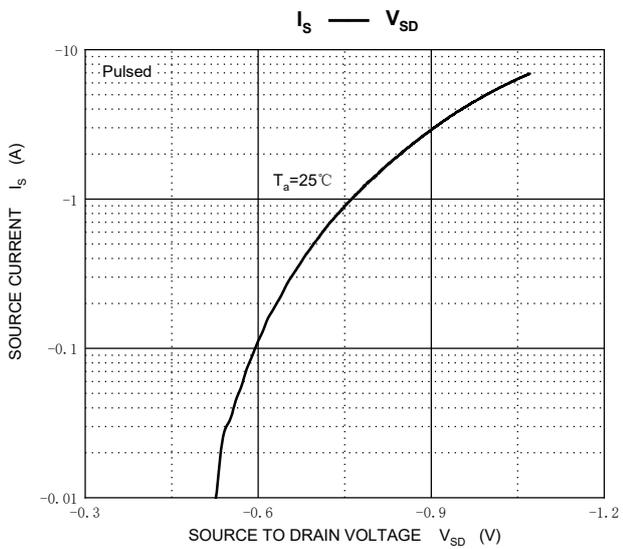
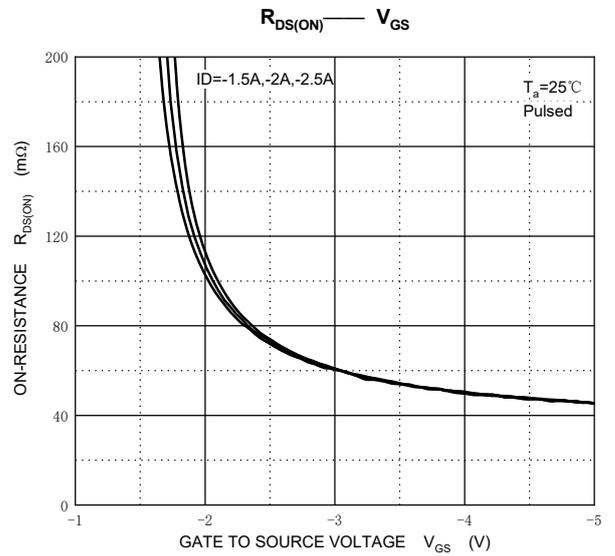
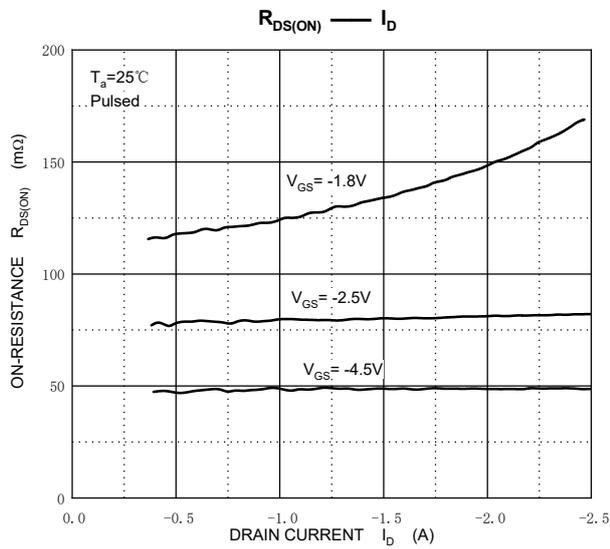
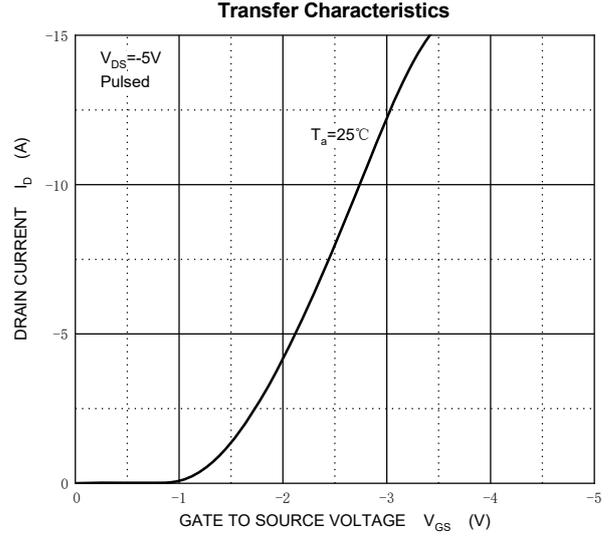
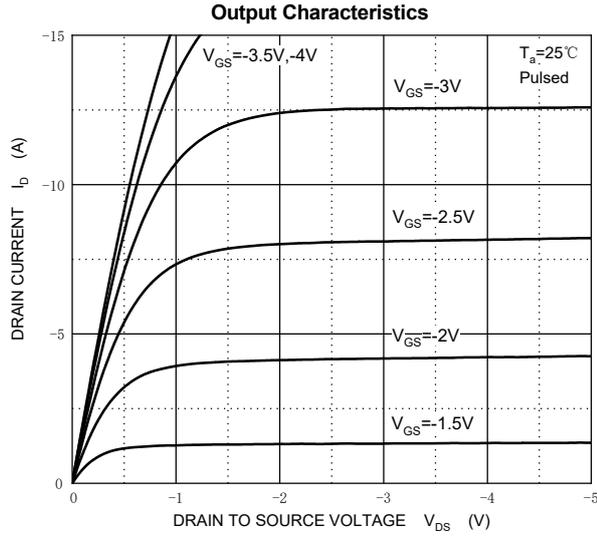
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±8	V
Continuous Drain Current	I_D	-2.8	A
Power Dissipation	P_D^a	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^{\circ}C/W$
Operation Junction and Storage Temperature Range	T_J, T_{STG}	-55~ +150	$^{\circ}C$

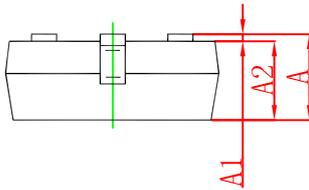
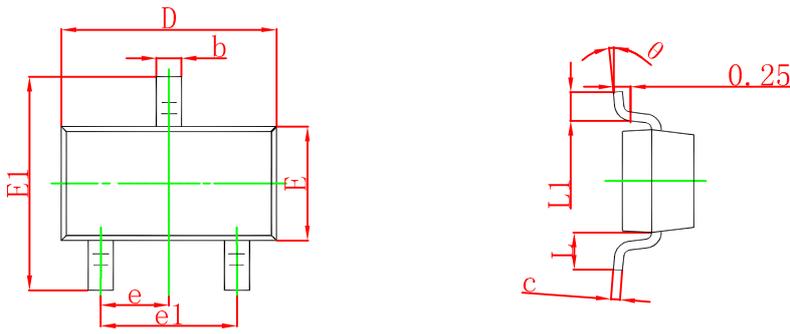
a. Device mounted on no heat sink.

$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$			-1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 8V, V_{DS} = 0V$			± 0.1	μA
Gate threshold voltage (note 1)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4	-0.626	-1	V
Drain-source on-resistance (note 1)	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -2.5A$	30	48	60	m Ω
		$V_{GS} = -2.5V, I_D = -2A$	40	70.5	85	
		$V_{GS} = -1.8V, I_D = -1.5A$	90	130	160	
Forward transconductance (note 1)	g_{FS}	$V_{DS} = -10V, I_D = -2.5A$	3		10	S
Dynamic characteristics (note 2)						
Input Capacitance	C_{iss}	$V_{DS} = -8V, V_{GS} = 0V, f = 1MHz$		640		pF
Output Capacitance	C_{oss}			120		pF
Reverse Transfer Capacitance	C_{rss}			82		pF
Gate resistance	R_g	$f = 1MHz$		100		Ω
Total Gate Charge	Q_g	$V_{DS} = -10V, V_{GS} = -4.5V, I_D = -2.5A$		5.5	10	nC
		$V_{DS} = -10V, V_{GS} = -2.5V, I_D = -2.5A$		3.3	6	nC
Gate-Source Charge	Q_{gs}	$V_{DS} = -10V, V_{GS} = -2.5V, I_D = -2.5A$		0.7		nC
Gate-Drain Charge	Q_{gd}	$V_{DS} = -10V, V_{GS} = -2.5V, I_D = -2.5A$		1.3		nC
Source-Drain Diode characteristics						
Diode forward current	I_S	$T_C = 25^\circ C$			-2.8	A
Diode Forward voltage (note 1)	V_{DS}	$V_{GS}, I_S = -2A$			-1.2	V

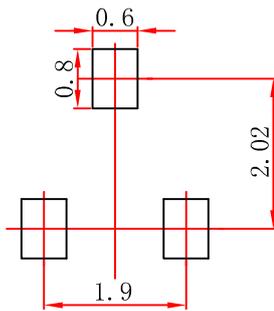
- Notes :**
1. Pulse test; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 2. Guaranteed by design, not subject to production testing.





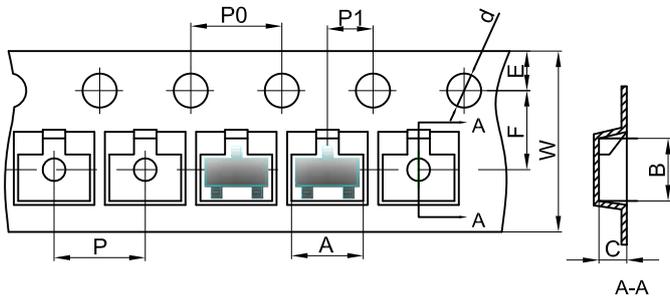
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



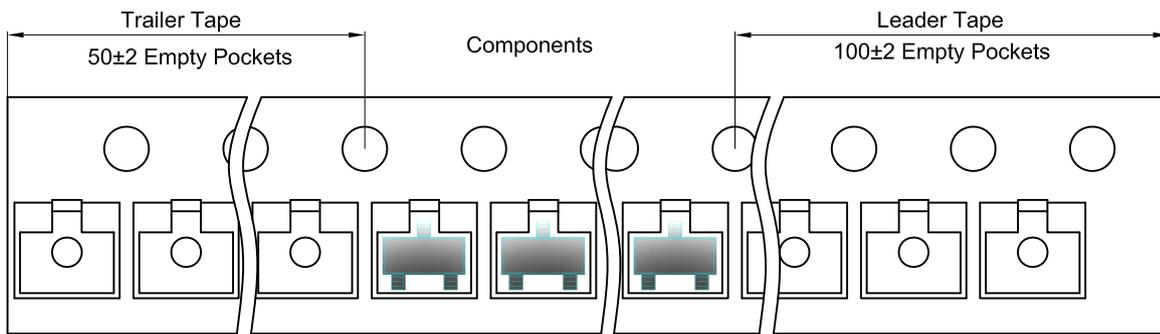
- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.05 mm.
 3. The pad layout is for reference purposes only.

SOT-23 Embossed Carrier Tape

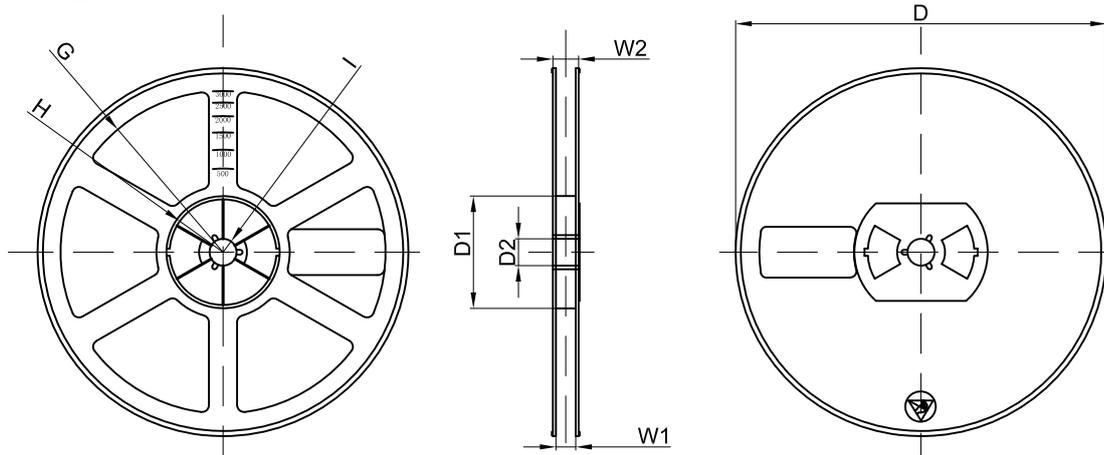


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23 Tape Leader and Trailer



SOT-23 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7"Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	
3000 pcs	7 inch	